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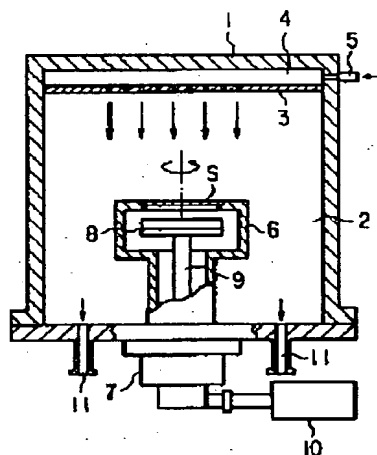
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## (54) SUBSTRATE TREATING DEVICE

## (57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a substrate treating device capable of sufficiently assuring the thermal and mechanical strength of a structural element heated to a temp. approximately equal to the temp. of a substrate to be treated and exhibiting stable functions over a long period of time.

**SOLUTION:** A semiconductor wafer S as the substrate to be treated is supported by a substrate holder 6 of this substrate treating device. This semiconductor wafer S is held at 300 to 1200°C and while the substrate holder 6 is rotated at the number of revolutions of 500 per minute, the semiconductor wafer S is subjected to a prescribed treatment by a vapor growth method. The substrate holder 6 is formed of a carbon fiber reinforced composite material consisting essentially of carbon and an SiC layer is formed on its surface.



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